

TC1174

300mA CMOS LDO with Shutdown and V_{REF} Bypass

Features

- Extremely Low Supply Current (50μA, Typ.)
- · Very Low Dropout Voltage
- 300mA Output Current
- · Adjustable Output Voltages
- · Power Saving Shutdown Mode
- · Bypass Input for Ultra Quiet Operation
- · Over Current and Over Temperature Protection
- · Space-Saving MSOP Package Option

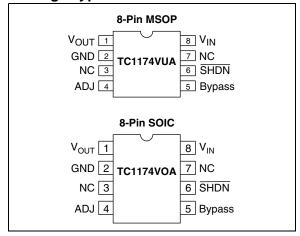
Applications

- · Battery Operated Systems
- Portable Computers
- · Medical Instruments
- Instrumentation
- Cellular/GSM/PHS Phones
- · Linear Post-Regulators for SMPS
- Pagers

Device Selection Table

Part Number	Output Voltage (V)	Package	Junction Temp. Range
TC1174VOA	Adjustable	8-Pin SOIC	-40°C to +125°C
TC1174VUA	Adjustable	8-Pin MSOP	-40°C to +125°C

Package Type



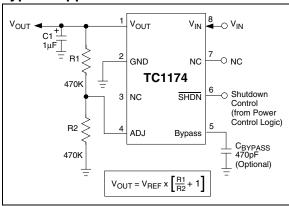
General Description

The TC1174 is an adjustable output CMOS low dropout regulator. Total supply current is typically $50\mu A$ at full load (20 to 60 times lower than in bipolar regulators).

TC1174 key features include ultra low noise operation (plus optional Bypass input); very low dropout voltage (typically 270mV at full load) and internal feed-forward compensation for fast response to step changes in load. Supply current is reduced to $0.05\mu A$ (typical) and V_{OLIT} falls to zero when the shutdown input is low.

The TC1174 incorporates both over temperature and over current protection. The TC1174 is stable with an output capacitor of only $1\mu F$ and has a maximum output current of 300mA.

Typical Application



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings*

 *Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

TC1174 ELECTRICAL SPECIFICATIONS

Symbol	Parameter	Min	Тур	Max	Units	Test Conditions
V _{IN}	Input Operating Voltage	2.7	_	6.0	V	Note 6
I _{OUTMAX}	Maximum Output Current	300	_	_	mA	
V _{REF}	Reference Voltage	1.165	1.20	1.235	V	
$\Delta V_{OUT}/\Delta T$	V _{OUT} Temperature Coefficient	_	40	_	ppm/°C	Note 1
$\Delta V_{OUT}/\Delta V_{IN}$	Line Regulation	_	0.05	0.35	%	$(V_R + 1V) \le V_{IN} \le 6V$
$\Delta V_{OUT}/V_{OUT}$	Load Regulation	_	1.1	2.0	%	$I_L = 0.1$ mA to $I_{OUT_{MAX}}$ (Note 2)
V _{IN} -V _{OUT}	Dropout Voltage	_ _ _	20 80 270	30 160 480	mV	$I_L = 0.1 \text{mA}$ $I_L = 100 \text{mA}$ $I_L = 300 \text{mA}$ (Note 3)
I _{SS1}	Supply Current	_	50	90	μΑ	SHDN = V _{IH}
I _{SS2}	Shutdown Supply Current	_	0.05	0.5	μΑ	SHDN = 0V
PSRR	Power Supply Rejection Ratio	_	60	_	dB	F _{RE} – 1kHz
I _{OUTSC}	Output Short Circuit Current	_	550	650	mA	V _{OUT} = 0V
$\Delta V_{OUT}/\Delta P_{D}$	Thermal Regulation	_	0.04	_	V/W	Note 4
eN	Output Noise	_	260	_	nV/√ Hz	$F = 10kHz$, $I_L = I_{OUTMAX}$ 470pF from Bypass to GND
SHDN Input						
V _{IH}	SHDN Input High Threshold	45	_	_	%V _{IN}	
V _{IL}	SHDN Input Low Threshold	_	_	15	%V _{IN}	
ADJ Input				•		'

- 1: TC $V_{OUT} = \frac{(V_{OUTMAX} V_{OUTMIN}) \times 10^6}{V_{OUT} \times \Delta T}$
- 2: Regulation is measured at a constant junction temperature using low duty cycle pulse testing. Load regulation is tested over a load range from 0.1mA to the maximum specified output current. Changes in output voltage due to heating effects are covered by the thermal regulation specification.
- 3: Dropout voltage is defined as the input to output differential at which the output voltage drops 2% below its nominal value measured at a 1V differential.
- 4: Thermal Regulation is defined as the change in output voltage at a time T after a change in power dissipation is applied, excluding load or line regulation effects. Specifications are for a current pulse equal to 1....... at V_{vv} = 6V for T = 10 msec
- line regulation effects. Specifications are for a current pulse equal to I_{LMAX} at V_{IN} = 6V for T = 10 msec.
 The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction-to-air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation causes the device to initiate thermal shutdown. Please see Section 4.0 Thermal Considerations for more details.
- 6: The minimum V_{IN} has to justify the conditions: $V_{IN} \ge V_R + V_{DROPOUT}$ and $V_{IN} \ge 2.7V$ for $I_L = 0.1 \text{mA}$ to $I_{OUT_{MAX}}$.

2.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 2-1.

TABLE 2-1: PIN FUNCTION TABLE

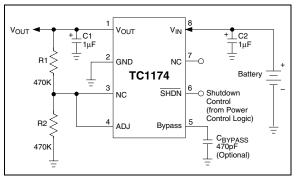
Pin No. (8-Pin SOIC) (8-Pin MSOP)	Symbol	Description
1	V _{OUT}	Regulated voltage output.
2	GND	Ground terminal.
3	NC	No connect.
4	ADJ	Output voltage adjust terminal. Output voltage setting is programmed with a resistor divider from V _{OUT} to this input. A capacitor may also be added to this input to reduce output noise.
5	Bypass	Reference bypass input. Connecting a 470pF to this input further reduces output noise.
6	SHDN	Shutdown control input. The regulator is fully enabled when a logic high is applied to this input. The regulator enters shutdown when a logic low is applied to this input. During shutdown, output voltage falls to zero and supply current is reduced to 0.05µA (typical).
7	NC	No connect.
8	V_{IN}	Unregulated supply input.

3.0 DETAILED DESCRIPTION

The TC1174 is an adjustable low drop-out regulator. Unlike bipolar regulators, the TC1174's supply current does not increase with load current. In addition, V_{OUT} remains stable and within regulation over the entire 0mA to I_{OUTMAX} operating load current range, (an important consideration in RTC and CMOS RAM battery back-up applications).

Figure 3-1 shows a typical application circuit. The regulator is enabled any time the shutdown input (SHDN) is at or above V $_{IH}$, and shutdown (disabled) when SHDN is at or below V $_{IL}$. SHDN may be controlled by a CMOS logic gate, or I/O port of a microcontroller. If the SHDN input is not required, it should be connected directly to the input supply. While in shutdown, supply current decreases to $0.05\mu A$ (typical), V_{OUT} falls to zero.

FIGURE 3-1: TYPICAL APPLICATION CIRCUIT



3.1 Bypass Input

A 470pF capacitor connected from the Bypass input to ground reduces noise present on the internal reference, which in turn significantly reduces output noise. If output noise is not a concern, this input may be left unconnected. Larger capacitor values may be used, but results in a longer time period to rated output voltage when power is initially applied.

3.2 Output Capacitor

A 1µF (min) capacitor from V_{OUT} to ground is required. The output capacitor should have an effective series resistance greater than 0.1Ω and less than 5.0Ω . A $1\mu\text{F}$ capacitor should be connected from V_{IN} to GND if there is more than 10 inches of wire between the regulator and the AC filter capacitor, or if a battery is used as the power source. Aluminum electrolytic or tantalum capacitor types can be used. (Since many aluminum electrolytic capacitors freeze at approximately -30°C, solid tantalums are recommended for applications operating below -25°C.) When operating from sources other than batteries, supply-noise rejection and transient response can be improved by increasing the value of the input and output capacitors and employing passive filtering techniques.

3.3 Adjust Input

The output voltage setting is determined by the values of R1 and R2 (Figure 3-1). The ohmic values of these resistors should be between 470K and 3M to minimize bleeder current.

The output voltage setting is calculated using the following equation.

EQUATION 3-1:

$$V_{OUT} = V_{REF} x \left[\frac{R1}{R2} + 1 \right]$$

The voltage adjustment range of the TC1174 is from V_{REF} to $(V_{IN}-0.05V)$.

4.0 THERMAL CONSIDERATIONS

4.1 Thermal Shutdown

Integrated thermal protection circuitry shuts the regulator off when die temperature exceeds 150°C. The regulator remains off until the die temperature drops to approximately 140°C.

4.2 Power Dissipation

The amount of power the regulator dissipates is primarily a function of input and output voltage, and output current. The following equation is used to calculate worst case actual power dissipation:

EQUATION 4-1:

$$P_D \approx (V_{INMAX} - V_{OUTMIN})I_{LOADMAX}$$

Where:

P_D = Worst case actual power dissipation

 V_{INMAX} = Maximum voltage on V_{IN}

V_{OUTMIN} = Minimum regulator output voltage

I_{LOADMAX} = Maximum output (load) current

The maximum allowable power dissipation (Equation 4-2) is a function of the maximum ambient temperature (T_{AMAX}), the maximum allowable die temperature (T_{JMAX}) and the thermal resistance from junction-to-air (θ_{JA}). The 8-Pin SOIC package has a θ_{JA} of approximately 160°C/Watt, while the 8-Pin MSOP package has a θ_{JA} of approximately 200°C/Watt.

EQUATION 4-2:

$$\mathsf{P}_{\mathsf{DMAX}} = \underbrace{(\mathsf{T}_{\mathsf{JMAX}} - \mathsf{T}_{\mathsf{AMAX}})}_{\theta_{\mathsf{JA}}}$$

Where all terms are previously defined.

Equation 4-1 can be used in conjunction with Equation 4-2 to ensure regulator thermal operation is within limits. For example:

Given:

 $V_{INMAX} = 3.0V + 10\%$ $V_{OUTMIN} = 2.7V - 0.5\%$ $I_{LOADMAX} = 250\text{mA}$ $T_{JMAX} = 125^{\circ}\text{C}$ $T_{AMAX} = 55^{\circ}\text{C}$

8-Pin MSOP Package

Find: 1. Actual power dissipation
2. Maximum allowable dissipation

Actual power dissipation:

$$P_D \approx (V_{INMAX} - V_{OUTMIN})I_{LOADMAX}$$

= [(3.0 x 1.1) - (2.7 x .995)]250 x 10⁻³
= 155mW

Maximum allowable power dissipation:

$$P_{DMAX} = \frac{(T_{JMAX} - T_{AMAX})}{\theta_{JA}}$$
$$= \frac{(125 - 55)}{200}$$
$$= 350 \text{mW}$$

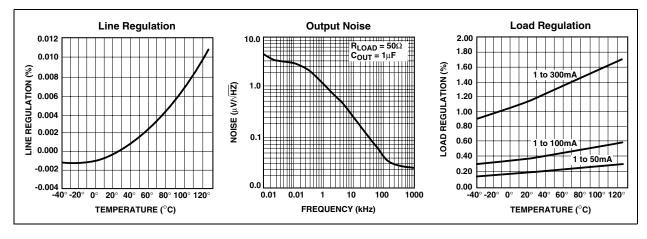
In this example, the TC1174 dissipates a maximum of 155mW; below the allowable limit of 350mW. In a similar manner, Equation 4-1 and Equation 4-2 can be used to calculate maximum current and/or input voltage limits. For example, the maximum allowable V_{IN} is found by substituting the maximum allowable power dissipation of 350mW into Equation 4-1, from which $V_{INMAX} = 4.1V$.

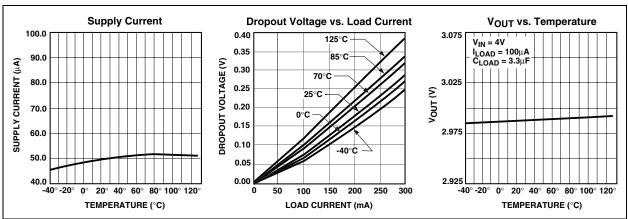
4.3 Layout Considerations

The primary path of heat conduction out of the package is via the package leads. Therefore, layouts having a ground plane, wide traces at the pads, and wide power supply bus lines combine to lower θ_{JA} and therefore increase the maximum allowable power dissipation limit.

5.0 TYPICAL CHARACTERISTICS

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.



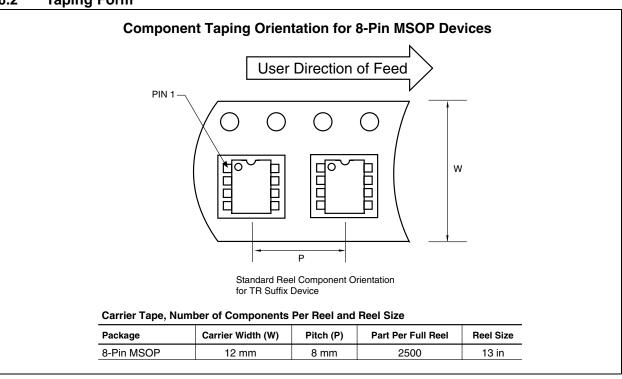


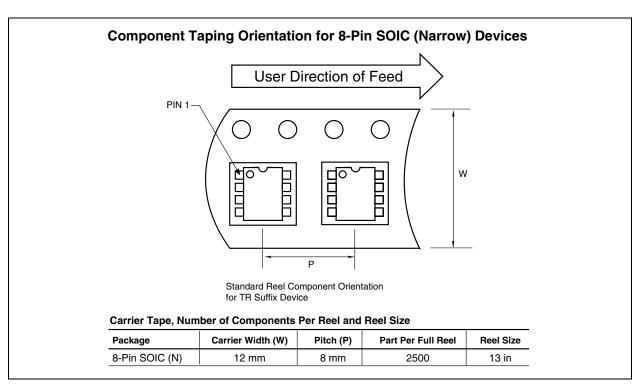
6.0 PACKAGING INFORMATION

6.1 Package Marking Information

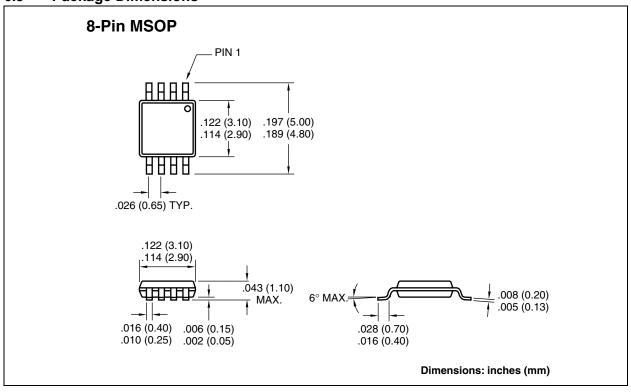
Package marking data not available at this time.

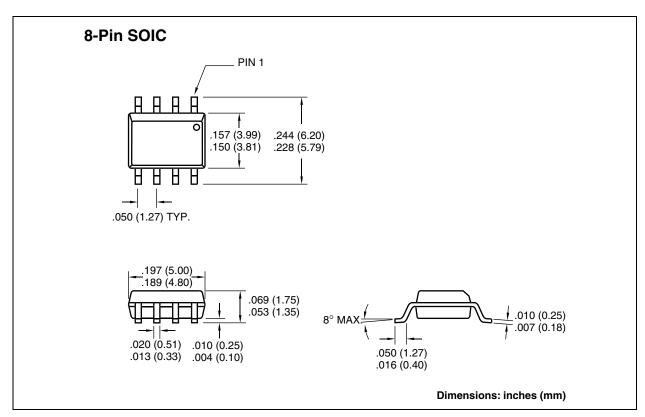
6.2 Taping Form





6.3 Package Dimensions





SALES AND SUPPORT

Data Sheets

Products supported by a preliminary Data Sheet may have an errata sheet describing minor operational differences and recommended workarounds. To determine if an errata sheet exists for a particular device, please contact one of the following:

- Your local Microchip sales office
- 1. 2. The Microchip Corporate Literature Center U.S. FAX: (480) 792-7277
- The Microchip Worldwide Site (www.microchip.com) 3.

Please specify which device, revision of silicon and Data Sheet (include Literature #) you are using.

New Customer Notification System
Register on our web site (www.microchip.com/cn) to receive the most current information on our products.

TC1174

NOTES:

Information contained in this publication regarding device applications and the like is intended through suggestion only and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. No representation or warranty is given and no liability is assumed by Microchip Technology Incorporated with respect to the accuracy or use of such information, or infringement of patents or other intellectual property rights arising from such use or otherwise. Use of Microchip's products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, under any intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, FilterLab, KEELOQ, microID, MPLAB, PIC, PICmicro, PICMASTER, PICSTART, PRO MATE, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

dsPIC, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, microPort, Migratable Memory, MPASM, MPLIB, MPLINK, MPSIM, MXDEV, MXLAB, PICC, PICDEM, PICDEM.net, rfPIC, Select Mode and Total Endurance are trademarks of Microchip Technology Incorporated in the U.S.A.

Serialized Quick Turn Programming (SQTP) is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2002, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.





Microchip received QS-9000 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona in July 1999 and Mountain View, California in March 2002. The Company's quality system processes and procedures are QS-9000 compliant for its PICmicro® 8-bit MCUs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, non-volatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: 480-792-7627 Web Address: http://www.microchip.com

Rocky Mountain

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7966 Fax: 480-792-7456

Atlanta

500 Sugar Mill Road, Suite 200B Atlanta, GA 30350

Tel: 770-640-0034 Fax: 770-640-0307

Boston

2 Lan Drive, Suite 120 Westford, MA 01886 Tel: 978-692-3848 Fax: 978-692-3821

Chicago

333 Pierce Road, Suite 180 Itasca, IL 60143

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

4570 Westgrove Drive, Suite 160 Addison, TX 75001 Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Tri-Atria Office Building 32255 Northwestern Highway, Suite 190 Farmington Hills, MI 48334 Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

2767 S. Albright Road Kokomo, Indiana 46902 Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

18201 Von Karman, Suite 1090 Irvine, CA 92612

Tel: 949-263-1888 Fax: 949-263-1338

New York

150 Motor Parkway, Suite 202 Hauppauge, NY 11788 Tel: 631-273-5305 Fax: 631-273-5335

San Jose

Microchip Technology Inc. 2107 North First Street, Suite 590 San Jose, CA 95131 Tel: 408-436-7950 Fax: 408-436-7955

6285 Northam Drive, Suite 108 Mississauga, Ontario L4V 1X5, Canada Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Australia

Microchip Technology Australia Pty Ltd Suite 22, 41 Rawson Street Epping 2121, NSW

Australia

Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing Microchip Technology Consulting (Shanghai)

Unit 915 Bei Hai Wan Tai Bldg. No. 6 Chaoyangmen Beidajie Beijing, 100027, No. China Tel: 86-10-85282100 Fax: 86-10-85282104

Co., Ltd., Beijing Liaison Office

China - Chengdu

Microchip Technology Consulting (Shanghai) Co., Ltd., Chengdu Liaison Office Rm. 2401, 24th Floor, Ming Xing Financial Tower No. 88 TIDU Street Chengdu 610016, China Tel: 86-28-86766200 Fax: 86-28-86766599

China - Fuzhou

Microchip Technology Consulting (Shanghai) Co., Ltd., Fuzhou Liaison Office Unit 28F, World Trade Plaza No. 71 Wusi Road Fuzhou 350001, China Tel: 86-591-7503506 Fax: 86-591-7503521

China - Shanghai

Microchip Technology Consulting (Shanghai)

Co., Ltd. Room 701, Bldg. B Far East International Plaza No. 317 Xian Xia Road Shanghai, 200051

Tel: 86-21-6275-5700 Fax: 86-21-6275-5060

China - Shenzhen

Microchip Technology Consulting (Shanghai) Co., Ltd., Shenzhen Liaison Office Rm. 1315, 13/F, Shenzhen Kerry Centre, Renminnan Lu

Shenzhen 518001, China

Tel: 86-755-2350361 Fax: 86-755-2366086

China - Hong Kong SAR

Microchip Technology Hongkong Ltd. Unit 901-6, Tower 2, Metroplaza 223 Hing Fong Road Kwai Fong, N.T., Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431

India

Microchip Technology Inc. India Liaison Office Divvasree Chambers 1 Floor, Wing A (A3/A4) No. 11, O'Shaugnessey Road Bangalore, 560 025, India Tel: 91-80-2290061 Fax: 91-80-2290062

Japan

Microchip Technology Japan K.K. Benex S-1 6F 3-18-20, Shinyokohama Kohoku-Ku, Yokohama-shi Kanagawa, 222-0033, Japan

Tel: 81-45-471-6166 Fax: 81-45-471-6122

Korea

Microchip Technology Korea 168-1, Youngbo Bldg. 3 Floor Samsung-Dong, Kangnam-Ku Seoul, Korea 135-882

Tel: 82-2-554-7200 Fax: 82-2-558-5934

Singapore

Microchip Technology Singapore Pte Ltd. 200 Middle Road #07-02 Prime Centre Singapore, 188980 Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan

Microchip Technology Taiwan 11F-3, No. 207 Tung Hua North Road Taipei, 105, Taiwan Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Denmark

Microchip Technology Nordic ApS Regus Business Centre Lautrup hoj 1-3 Ballerup DK-2750 Denmark Tel: 45 4420 9895 Fax: 45 4420 9910

France

Microchip Technology SARL Parc d'Activite du Moulin de Massy 43 Rue du Saule Trapu Batiment A - ler Etage 91300 Massy, France Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany

Microchip Technology GmbH Gustav-Heinemann Ring 125 D-81739 Munich, Germany Tel: 49-89-627-144 0 Fax: 49-89-627-144-44

Italy

Microchip Technology SRL Centro Direzionale Colleoni Palazzo Taurus 1 V. Le Colleoni 1 20041 Agrate Brianza Milan, Italy
Tel: 39-039-65791-1 Fax: 39-039-6899883

United Kingdom Microchip Ltd. 505 Eskdale Road Winnersh Triangle Wokingham

Berkshire, England RG41 5TU

Tel: 44 118 921 5869 Fax: 44-118 921-5820

05/01/02

